

#### Description

The DMP22D6UT uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

#### **General Features**

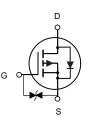
 $V_{DS} = -20V I_D = -0.66A$   $R_{DS(ON)} < 560 m\Omega@ V_{GS} = -4.5V$   $R_{DS(ON)} < 780 m\Omega@ V_{GS} = -2.5V$ ESD Rating: 1500V HBM

## Application

Battery protection Load switch Uninterruptible power supply







P-Channel MOSFET

#### Package Marking and Ordering Information

| Product ID | Pack    | Brand      | Qty(PCS) |  |
|------------|---------|------------|----------|--|
| DMP22D6UT  | SOT-523 | HXY MOSFET | 3000     |  |

## Absolute Maximum Ratings (T<sub>A</sub>=25<sup>°</sup>C unless otherwise noted)

| Parameter  | Limit  | Unit   |  |
|--|--|--|--|
| Drain-Source Voltage                             | -20  | V  |  |
| Gate-Source Voltage                              | ±12  | V  |  |
| Drain Current-Continuous                         | -0.66  | А  |  |
| Maximum Power Dissipation                        | 150  | mW   |  |
| Operating Junction and Storage Temperature Range | -55 To 150   | °C   |  |
| Thermal Resistance, Junction-to-Ambient (Note 2) | 833  | °C/W   |  |
|  | Drain-Source Voltage         Gate-Source Voltage         Drain Current-Continuous         Maximum Power Dissipation         Operating Junction and Storage Temperature Range | Drain-Source Voltage-20Gate-Source Voltage±12Drain Current-Continuous-0.66Maximum Power Dissipation150Operating Junction and Storage Temperature Range-55 To 150 |  |



| Parameter   | Symbol               | Test conditions   | Min  | Тур  | Max  | Unit |
|---|----------------------|---|------|------|------|------|
| STATIC CHARACTERISTICE                                      |                      |   |      |      |      |      |
| Drain-source breakdown voltage                              | V <sub>(BR)DSS</sub> | V <sub>GS</sub> = 0V, I <sub>D</sub> =-250µA              | -20  |      |      | V    |
| Zero gate voltage drain current                             | I <sub>DSS</sub>     | V <sub>DS</sub> =-20V,V <sub>GS</sub> = 0V                |      |      | -1   | μA   |
| Gate-body leakage current                                   | lgss                 | $V_{GS}$ =±10V, $V_{DS}$ = 0V                             |      |      | ±10  | μA   |
| Gate threshold voltage (note2)                              | $V_{\text{GS(th)}}$  | V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250µA | -0.4 | -0.7 | -1.0 | V    |
| Durain annual an an àirtean a                               | R <sub>DS(on)</sub>  | V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-0.5A             |      |      | 0.56 | Ω    |
| Drain-source on-resistance (note2)                          |                      | V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-0.2A             |      |      | 0.78 | Ω    |
| Maximum Continuous Drain to<br>Source Diode Forward Current | ls                   |   |      |      | -0.6 | А    |
| Maximum Pulsed Drain to Source<br>Diode Forward Current     | e I <sub>SM</sub>    |   |      | -1.2 | А    |      |
| Diode forward voltage                                       | V <sub>SD</sub>      | I <sub>S</sub> =-0.5A, V <sub>GS</sub> = 0V               |      |      | -1.2 | V    |
| DYNAMIC CHARACTERISTICS (note4)                             |                      |   |      |      |      | 1    |
| Input capacitance   | C <sub>iss</sub>     |   |      | 115  |      | pF   |
| Output capacitance  | Coss                 | V <sub>DS</sub> =-16V,V <sub>GS</sub> =0V,<br>f =1MHz     |      | 15   |      | pF   |
| Reverse transfer capacitance                                | C <sub>rss</sub>     |   |      | 9    |      | pF   |
| SWITCHING CHARACTERISTICS (no                               | te4)                 |   | I    |      |      | 1    |
| Turn-on delay time (note3)                                  | t <sub>d(on)</sub>   | V <sub>GS</sub> =-4.5V,V <sub>DS</sub> =-10V,             |      | 9    |      | nS   |
| Turn-on rise time (note3)                                   | tr                   |   |      | 6    |      | nS   |
| Turn-off delay time (note3)                                 | $t_{d(off)}$         | $I_D$ =-200mA,R <sub>GEN</sub> =10 $\Omega$               |      | 33   |      | nS   |
| Turn-off fall time (note3)                                  | t <sub>f</sub>       |   |      | 22   |      | nS   |

# Electrical Characteristics (TJ=25°C, unless otherwise noted)

Notes:

1. Surface mounted on FR4 board using the minimum recommended pad size.

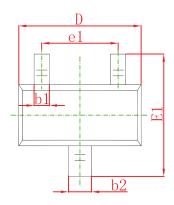
2. Pulse Test : Pulse Width=300µs, Duty Cycle=2%.

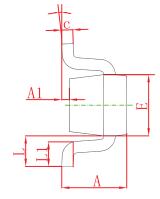
3. Switching characteristics are independent of operating junction temperatures.

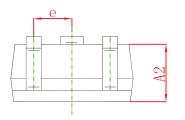
4. Guaranteed by design, not subject to producting.



## **SOT-523 Package Information**

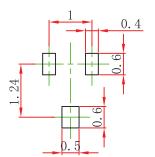






| Symbol | Dimensions In Millimeters |       | Dimensions In Inches |       |  |
|--------|---------------------------|-------|----------------------|-------|--|
| Symbol | Min.                      | Max.  | Min.                 | Max.  |  |
| A      | 0.700                     | 0.900 | 0.028                | 0.035 |  |
| A1     | 0.000                     | 0.100 | 0.000                | 0.004 |  |
| A2     | 0.700                     | 0.800 | 0.028                | 0.031 |  |
| b1     | 0.150                     | 0.250 | 0.006                | 0.010 |  |
| b2     | 0.250                     | 0.350 | 0.010                | 0.014 |  |
| С      | 0.100                     | 0.200 | 0.004                | 0.008 |  |
| D      | 1.500                     | 1.700 | 0.059                | 0.067 |  |
| E      | 0.700                     | 0.900 | 0.028                | 0.035 |  |
| E1     | 1.450                     | 1.750 | 0.057                | 0.069 |  |
| е      | 0.500 TYP.                |       | 0.020 TYP.           |       |  |
| e1     | 0.900                     | 1.100 | 0.035                | 0.043 |  |
| L      | 0.400 REF.                |       | 0.016 REF.           |       |  |
| L1     | 0.260                     | 0.460 | 0.010                | 0.018 |  |
| θ      | 0°                        | 8°    | 0°                   | 8°    |  |

## SOT-523 Suggested Pad Layout



Note:

1.Controlling dimension:in millimeters.

2.General tolerance:±0.05mm.

3. The pad layout is for reference purposes only.



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